

**SECONDARY EMISSION OF MCs_n^+ MOLECULAR IONS AND
ITS APPLICATIONS IN COMPOSITIONAL ANALYSIS OF
MBE GROWN Si-Ge STRUCTURES**

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Contents

1	Introduction	1
1.1	Present Trend in Ion Beam Analysis	2
1.2	Compositional Depth Profiling	4
1.3	Sputter Depth Profiling	5
1.3.1	Sputtering Time - Depth Conversion	7
1.3.2	Intensity - Concentration Conversion	8
1.3.3	Profile Shape Considerations: Depth Resolution	8
1.4	Secondary Ion Mass Spectrometry	10
1.4.1	Secondary Ion Emission and Matrix Effect	12
1.4.2	MCs ⁺ -SIMS Approach	13
1.5	Recent Growth Trends: Molecular Beam Epitaxy	14
1.6	MCs ⁺ -SIMS for Direct Compositional Analysis	16
1.7	Thesis Overview	17
2	Experimental Aspects	19
2.1	Growth Technique	19
2.1.1	Molecular Beam Epitaxy (MBE)	20
2.2	Surface and Interface Probes	34
2.2.1	Secondary Ion Mass Spectrometry (SIMS)	36
2.2.2	X-Ray Diffraction (XRD)	49
2.2.3	Atomic Force Microscopy (AFM)	56

2.2.4	Scanning Electron Microscopy (SEM)	59
2.2.5	Trasmission Electron Microscopy (TEM)	69
3	Matrix Effect Compensation: ‘MCs_n^+-SIMS’	77
3.1	Matrix Effect in Secondary Ion Mass Spectrometry	77
3.2	Elemental Quantification and MCs_n^+ -SIMS	79
3.3	Formation Mechanisms of MCs_n^+ Molecular Ions	83
3.3.1	Effect of Primary Impact Energy	84
3.3.2	Effect of Impact Angle	95
3.3.3	Role of Reactive Species	100
3.4	Concluding Remarks	114
4	Compositional Analysis of SiGe Alloy and Multilayers	116
4.1	SiGe Alloy and Matrix Effect Compensation	116
4.1.1	SiGe Alloy Film Deposition	119
4.1.2	Characterization of SiGe Alloy	119
4.1.3	Matrix Effect Compensation for SiGe Alloy	125
4.2	Si/Ge Multilayers and Compositional Analysis	127
4.2.1	Multilayer Deposition	128
4.2.2	Characterization of Si/Ge Multilayers	129
4.2.3	Direct Compositional Analysis of Si/Ge Mutilayers	133
4.3	Concluding Remarks	136
5	Conclusion	137
	Bibliography	141